

# Anatoly Druzhinin

## List of Publications by Year in descending order

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75  
papers

606  
citations

471509

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713466

21  
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75  
docs citations

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times ranked

137  
citing authors

#	ARTICLE	IF	CITATIONS
1	Critical fields and features of electromagnetic transport of Bi <sub>2</sub> Se <sub>3</sub> whiskers at low temperatures. Low Temperature Physics, 2021, 47, 96-100.	0.6	0
2	Quantum magnetoresistance in Si &lt;B, Ni&gt; whiskers. Low Temperature Physics, 2021, 47, 488-492.	0.6	1
3	Magneto-transport properties of Bi <sub>2</sub> Se <sub>3</sub> whiskers: superconductivity and weak localization. Molecular Crystals and Liquid Crystals, 2020, 701, 82-90.	0.9	0
4	Rashba Interaction in Polysilicon Layers SemOI-Structures. Journal of Electronic Materials, 2019, 48, 4934-4938.	2.2	4
5	Quantization in magnetoresistance of strained InSb whiskers. Low Temperature Physics, 2019, 45, 513-517.	0.6	2
6	Strain-Induced Berry Phase in GaSb Microcrystals. Journal of Low Temperature Physics, 2019, 196, 375-385.	1.4	2
7	Spin-orbit coupling in strained Ge whiskers. Low Temperature Physics, 2019, 45, 1182-1186.	0.6	2
8	Superconductivity and weak anti-localization in GaSb whiskers under strain. Low Temperature Physics, 2019, 45, 1065-1071.	0.6	4
9	Spin-related phenomena in nanoscale Si <B, Ni> whiskers. Journal of Magnetism and Magnetic Materials, 2019, 473, 331-334.	2.3	11
10	Superconductivity and weak localization of PdxBi <sub>2</sub> Se <sub>3</sub> whiskers at low temperatures. Applied Nanoscience (Switzerland), 2018, 8, 877-883.	3.1	6
11	Nanoscale polysilicon in sensors of physical values at cryogenic temperatures. Journal of Materials Science: Materials in Electronics, 2018, 29, 8364-8370.	2.2	6
12	Weak Antilocalization Model of N-Type Bi <sub>2</sub> Se <sub>3</sub> Whiskers. , 2018, , .		1
13	The spin-resolved electronic structure of doped crystals si&lt;Ni&gt; and Si&lt;B, Ni>: theoretical and experimental aspects. Molecular Crystals and Liquid Crystals, 2018, 674, 120-129.	0.9	3
14	Spin-orbit interaction in InSb core-shell wires. Molecular Crystals and Liquid Crystals, 2018, 674, 1-10.	0.9	4
15	Role of Ag-catalyst morphology and molarity of AgNO <sub>3</sub> on the size control of Si nanowires produced by metal-assisted chemical etching. Molecular Crystals and Liquid Crystals, 2018, 674, 69-75.	0.9	4
16	Spin-Dependent Transport of Charge Carriers in Silicon Microcrystals Doped with Boron and Diluted with Nickel. , 2018, , .		0
17	Berry phase in strained InSb whiskers. Low Temperature Physics, 2018, 44, 1189-1194.	0.6	12
18	Impedance of boron and nickel doped silicon whiskers. Molecular Crystals and Liquid Crystals, 2018, 661, 12-19.	0.9	7

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19	Fabrication and Characterization of High-Performance Anti-reflecting Nanotextured Si Surfaces for Solar Cells. Springer Proceedings in Physics, 2018, , 275-283.	0.2	10
20	Studies piezoresistive properties of n-type conductivity indium antimonide thin layers. , 2018, , .		0
21	3D MOS-transistor elements in smart-sensors based on SOI-structures. , 2018, , .		0
22	MSoC device based on SOI-structures. , 2018, , .		0
23	Development of anti-reflecting surfaces based on Si micropylramids and wet-chemically etched Si nanowire arrays. Functional Materials, 2018, 25, 675-680.	0.1	5
24	Silicon Nanostructures Produced by Modified MacEtch Method for Antireflective Si Surface. Nanoscale Research Letters, 2017, 12, 106.	5.7	23
25	Low-temperature magnetoresistance of GaSb whiskers. Low Temperature Physics, 2017, 43, 692-698.	0.6	17
26	Thermoelectric properties of SiGe whiskers with various morphology. , 2017, , .		0
27	Deformation characteristics of SOI structures at cryogenic temperatures. , 2017, , .		0
28	Peculiarities of magnetoresistance in Si whiskers doped Ni at cryogenic temperatures. , 2017, , .		0
29	The effect of hydrostatic pressure on the indium antimonide thin films. , 2017, , .		0
30	Nanoscale Conductive Channels in Silicon Whiskers with Nickel Impurity. Nanoscale Research Letters, 2017, 12, 78.	5.7	16
31	Properties of Doped GaSb Whiskers at Low Temperatures. Nanoscale Research Letters, 2017, 12, 156.	5.7	18
32	Magnetoresistance oscillations in InSb and GaSb whiskers at low temperatures. , 2017, , .		0
33	Magnetoresistance of doped Te:GaSb whiskers. , 2017, , .		0
34	Superconductivity and Kondo Effect of PdxBi2Se3 Whiskers at Low Temperatures. Journal of Nano- and Electronic Physics, 2017, 9, 05013-1-05013-5.	0.5	8
35	Properties of SiGe microcrystals in strong magnetic fields for thermoelectric sensors. , 2016, , .		0
36	Negative magnetoresistance in indium antimonide whiskers doped with tin. Low Temperature Physics, 2016, 42, 453-457.	0.6	19

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37	The frequency dependence features of Si whiskers conductance in low-temperature range. , 2016, , .		0
38	Silicon nanostructures formed by metal-assisted chemical etching for electron field emission cathodes. , 2016, , .		0
39	Micro- and Nanotextured Silicon for Antireflective Coatings of Solar Cells. Journal of Nano Research, 2016, 39, 89-95.	0.8	19
40	Antireflective properties of silicon modified by electrochemical and chemical methods. , 2016, , .		0
41	Electrical and layouts simulation of analytical microsystem-on-chip elements for high frequency and low temperature applications. , 2016, , .		0
42	Magnetoresistance oscillations in germanium and indium antimonide whiskers. , 2016, , .		0
43	Components of micro- and nanoelectronics based on silicon structures for cryogenic temperatures. , 2016, , .		0
44	Magnetic Properties of Doped Si&lt;B,Ni&gt; Whiskers for Spintronics. Journal of Nano Research, 2016, 39, 43-54.	0.8	18
45	GaSb whiskers in sensor electronics. Functional Materials, 2016, 23, 206-211.	0.1	9
46	Thermoelectric Properties of Oblique SiGe Whiskers. Journal of Nano- and Electronic Physics, 2016, 8, 02030-1-02030-5.	0.5	3
47	Strain-induced effects in p-type Si whiskers at low temperatures. Materials Science in Semiconductor Processing, 2015, 40, 766-771.	4.0	27
48	Magnetic susceptibility and magnetoresistance of neutron-irradiated doped Si whiskers. Journal of Magnetism and Magnetic Materials, 2015, 393, 310-315.	2.3	19
49	Low temperature magnetoresistance of InSb whiskers. Materials Science in Semiconductor Processing, 2015, 40, 550-555.	4.0	21
50	Modification of silicon surface for solar cells. , 2015, , .		3
51	Peculiarities of magnetoresistance in InSb whiskers at cryogenic temperatures. Materials Research Bulletin, 2015, 72, 324-330.	5.2	17
52	Magneto-transport properties of poly-silicon in SOI structures at low temperatures. Materials Science in Semiconductor Processing, 2015, 31, 19-26.	4.0	20
53	Peculiarities of charge carriers transport in submicron Si-Ge whiskers. Functional Materials, 2015, 22, 27-33.	0.1	2
54	Variable-temperature hopping conductance in Si whiskers. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 504-508.	1.8	20

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55	Impedance spectroscopy of polysilicon in SOI structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 156-159.	0.8	17
56	Properties of Low-Dimensional Polysilicon in SOI Structures for Low Temperature Sensors. <i>Advanced Materials Research</i> , 2013, 854, 49-55.	0.3	19
57	High Sensitive Active MOS Photo Detector on the Local 3D SOI-Structure. <i>Advanced Materials Research</i> , 2013, 854, 45-47.	0.3	17
58	Magnetic Susceptibility of Doped Si Nanowhiskers. <i>Journal of Nanoscience and Nanotechnology</i> , 2012, 12, 8690-8693.	0.9	15
59	Si and Si-Ge wires for thermoelectrics. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 867-870.	0.8	7
60	Strain effect on magnetoresistance of SiGe solid solution whiskers at low temperatures. <i>Materials Science in Semiconductor Processing</i> , 2011, 14, 18-22.	4.0	24
61	3D SOI Elements for System-on-Chip Applications. <i>Advanced Materials Research</i> , 2011, 276, 137-144.	0.3	4
62	Polysilicon on Insulator Structures for Sensor Application at Electron Irradiation & Magnetic Fields. <i>Advanced Materials Research</i> , 2011, 276, 109-116.	0.3	16
63	Alternating Current Converter. , 2006, , .		0
64	Thermoelectric properties of Si-Ge whiskers. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 853-857.	4.0	8
65	Study of piezoresistance in $GexSi_{1-x}$ whiskers for sensor application. <i>Materials Science in Semiconductor Processing</i> , 2005, 8, 193-196.	4.0	12
66	Investigation of Si-Ge whisker growth by CVD. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 333-336.	0.8	16
67	Composition and Electrical Properties of $Hg_xCd_{1-x}S$ Whiskers. <i>Inorganic Materials</i> , 2002, 38, 336-338.	0.8	0
68	Investigation of free and strained germanium whiskers at cryogenic temperatures. , 2001, 4413, 143.		3
69	Low-temperature semiconductor mechanical sensors. <i>Sensors and Actuators A: Physical</i> , 2000, 85, 153-157.	4.1	36
70	Medical pressure sensors on the basis of silicon microcrystals and SOI layers. <i>Sensors and Actuators B: Chemical</i> , 1999, 58, 415-419.	7.8	25
71	Physical aspects of multifunctional sensors based on piezothermomagnetic effects in semiconductors. <i>Sensors and Actuators A: Physical</i> , 1998, 68, 229-233.	4.1	3
72	Laser-recrystallized polysilicon layers in sensors. <i>Sensors and Actuators A: Physical</i> , 1992, 30, 143-147.	4.1	16

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73	FEM model of thermoelectric sensor sensitive element based on silicon whiskers. , 0, , .		0
74	Formation of Ordered Si Nanowires Arrays on Si Substrate. Advanced Materials Research, 0, 854, 83-88.	0.3	5
75	Strain-induced splitting in valence band of Siâ€“Ge whiskers. Applied Nanoscience (Switzerland), 0, , 1.	3.1	0